

## SANYO Semiconductors

### DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

# **BFL4037** — General-Purpose Switching Device Applications

#### **Features**

- ON-resistance RDS(on)= $0.33\Omega$  (typ.)
- Input capacitance Ciss=1200pF (typ.)
- 10V drive

#### **Specifications**

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		500	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I <sub>Dc</sub> *1	Limited only by maximum temperature Tch=150°C	16	А
	I <sub>Dpack</sub> *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	11	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	А
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		159	mJ
Avalanche Current *5	I <sub>AV</sub>		16	А

Note: \*1 Shows chip capability

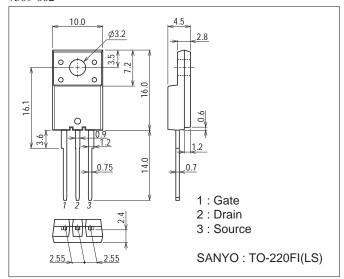
- \*2 Package limited
- \*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

- \*4 VDD=99V, L=1mH, IAV=16A (Fig.1)
- \*5 L≤1mH, single pulse

#### **Package Dimensions**

unit : mm (typ) 7509-002



#### **Product & Package Information**

• Package : TO-220FI(LS)

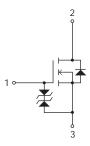
• JEITA, JEDEC : SC-67, SOT-186A, TO-220F

• Minimum Packing Quantity: 100 pcs./bag or 50pcs./magazine

#### Marking

# FL4037

#### **Electrical Connection**



**SANYO Semiconductor Co., Ltd.** 

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Uniit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	500			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =400V, V <sub>GS</sub> =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±24V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	3		5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =8A	4.5	9		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)	I <sub>D</sub> =8A, V <sub>G</sub> S=10V		0.33	0.43	Ω
Input Capacitance	Ciss	V <sub>DS</sub> =30V, f=1MHz		1200		pF
Output Capacitance	Coss	V <sub>DS</sub> =30V, f=1MHz		250		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =30V, f=1MHz		55		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See Fig.2		26.5		ns
Rise Time	t <sub>r</sub>	See Fig.2		78		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See Fig.2		146		ns
Fall Time	tf	See Fig.2		57		ns
Total Gate Charge	Qg	V <sub>D</sub> S=200V, V <sub>G</sub> S=10V, I <sub>D</sub> =16A		48.6		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V, I <sub>D</sub> =16A		8.2		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V, I <sub>D</sub> =16A		27.4		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =16A, V <sub>GS</sub> =0V		0.95	1.3	V
Reverse Recovery Time	t <sub>rr</sub>	See Fig.3		600		ns
Reverse Recovery Charge	Qrr	IS=16A, VGS=0V, di/dt=100A/μs		5000		nC

Fig.1 Avalanche Resistance Test Circuit

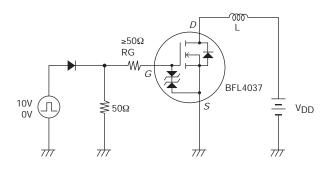


Fig.2 Switching Time Test Circuit

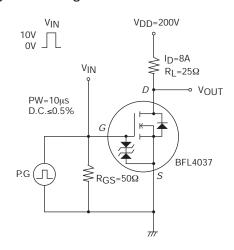
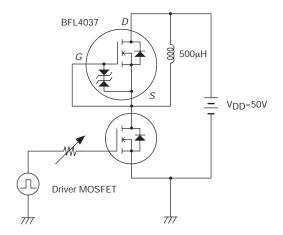
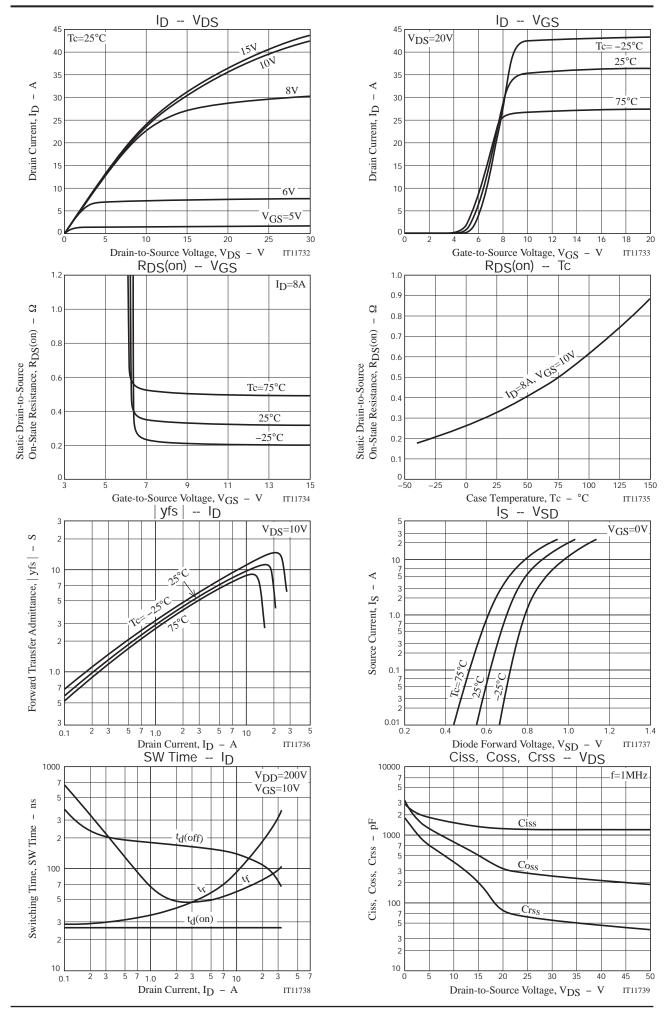
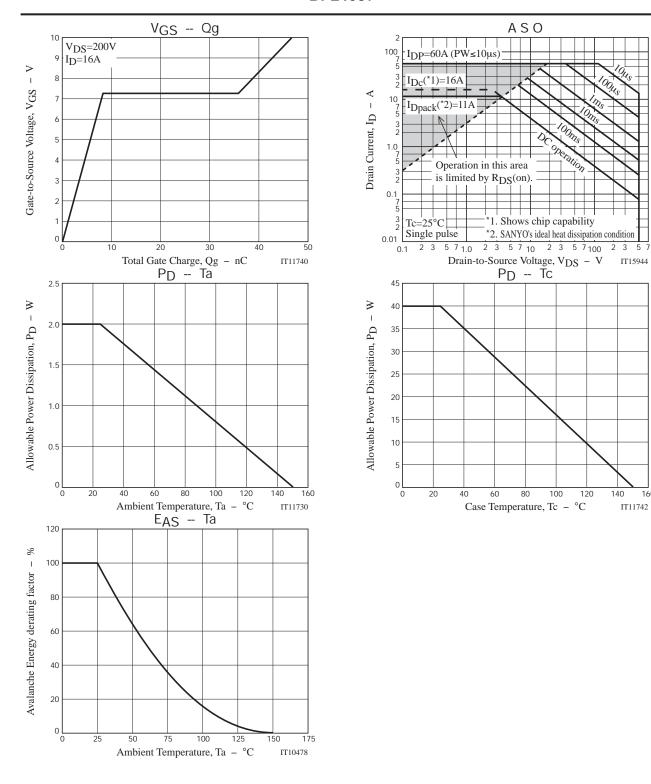


Fig.3 Reverse Recovery Time Test Circuit







140

160

IT11742

Note on usage : Since the BFL4037 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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